

HEXFET® Power MOSFETs



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Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 70° (A)	R_{θ} Max. Thermal Resistance † (°C/W)	P_D Max. Power Dissipation † (W)	VFM Forward Voltage Drop @ T_J = 25°C	Fax on Demand Number	Case Outline Key
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Surface Mount Packages

FETKY Micro8

FETKY (Co-packaged HEXFET Power MOSFET and Schottky Diode)

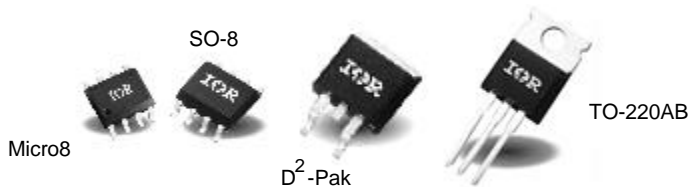
N-Channel

IRF7521D1	20	0.135	2.4	1.9	100	1.25	0.50 @ 1.0A	91646
IRF7523D1	30	0.135	2.4	1.9	100	0.8	0.50 @ 1.0A	91647

P-Channel

IRF7524D1	-20	0.27	-1.7	-1.4	100	0.8	0.50 @ 1.0A	91648
IRF7526D1	-30	0.27	-1.7	-1.4	100	0.8	0.50 @ 1.0A	91649

† Measured at ambient for Micro8 and SO-8 package styles. All others measured at case.



Illustrations not to scale



To view a datasheet, click on the part number

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Surface Mount Packages

FETKY SO-8

FETKY (Co-packaged HEXFET Power MOSFET and Schottky Diode)

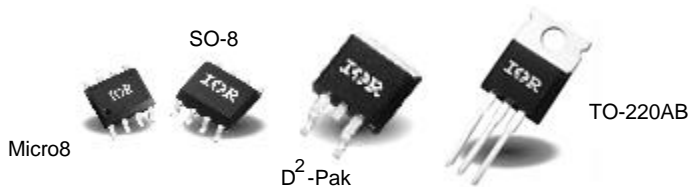
N-Channel

IRF7421D1	30	0.035	4.1	3.3	50	1.0	0.50 @ 1.0A	91411	H5
IRF7422D2	-20	0.09	-2.9	-2.3	50	1.0	0.57 @ 3.0A	91412	

P-Channel

IRF7321D2	-30	0.058	-4.9	-3.9	62.5	2.0	0.57 @ 3.0A	91667	H5
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Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100° (A)	R_{θ} Max. Thermal Resistance † ($^{\circ}C/W$)	P_D Max. Power Dissipation † (W)	Fax on Demand Number	Case Outline Key
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Surface Mount Packages

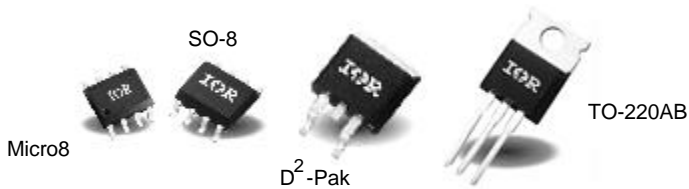
D2Pak

FETKY (Co-packaged HEXFET Power MOSFET and Schottky Diode): Logic Level

N-Channel

IRL3103D1S	30	0.014	54	34	1.8	3.1	91558	H10
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Illustrations not to scale



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Part Number	$V_{(BR)DSS}$ Drain-to-Source Breakdown Voltage (V)	$R_{DS(on)}$ On-State Resistance (Ω)	I_D Continuous Drain Current 25°C (A)	I_D Continuous Drain Current 100° (A)	R_{θ} Max. Thermal Resistance † ($^{\circ}C/W$)	P_D Max. Power Dissipation † (W)	Fax on Demand Number	Case Outline Key
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Through-Hole Packages

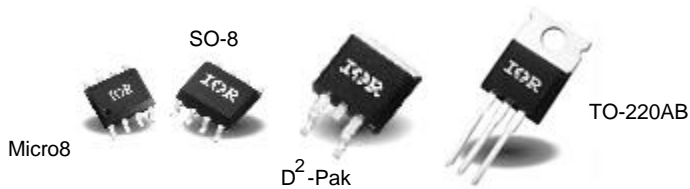
TO-220AB

FETKY (Co-packaged HEXFET Power MOSFET and Schottky Diode): Logic Level

N-Channel

IRL3103D1	30	0.014	54	34	1.8	2	91608	H12
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† Measured at ambient for Micro8 and SO-8 package styles. All others measured at case.



Illustrations not to scale



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